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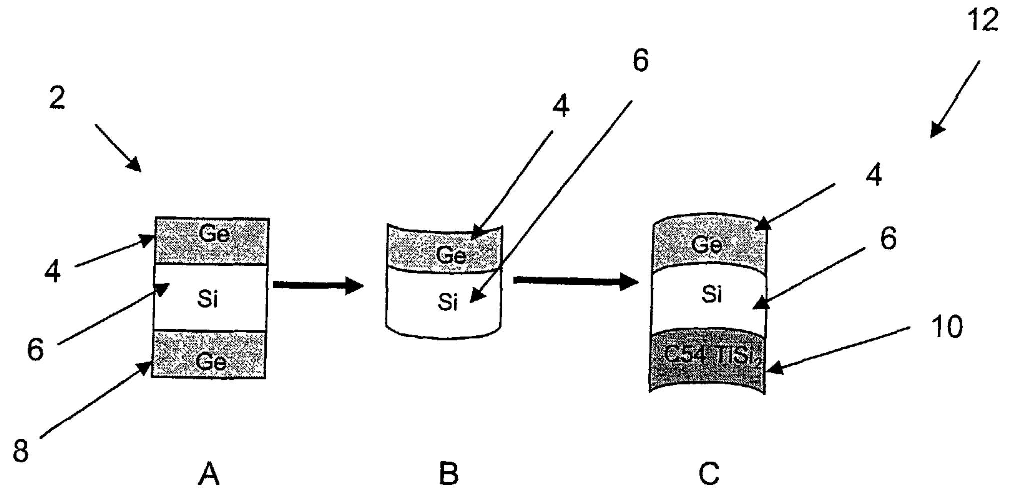
(54) Title: METHOD AND STRUCTURE OF STRAIN CONTROL OF SiGe BASED PHOTODETECTORS AND MODULATORS



(57) Abstract: A SiGe or Ge structure comprises a substrate and a SiGe or Ge layer that is formed on a first surface of the substrate. A silicidation or germanide layer is formed on a second surface of the substrate so to increase the tensile strain of the SiGe or Ge layer on the first surface.

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A. CLASSIFICATION OF SUBJECT MATTER
IPC 7 H01L21/20 C30B25/18

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
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Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, INSPEC

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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P,X	WO 2004/001857 A (MASSACHUSETTS INSTITUTE OF TECHNOLOGY) 31 December 2003 (2003-12-31) claims; figure 1 -----	27
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☒ Further documents are listed in the continuation of box C.

☒ Patent family members are listed in annex.

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Date of the actual completion of the international search 14 March 2005	Date of mailing of the international search report 22/03/2005
Name and mailing address of the ISA European Patent Office, P.B. 5818 Patentlaan 2 NL – 2280 HV Rijswijk Tel. (+31-70) 340-2040, Tx. 31 651 epo nl, Fax: (+31-70) 340-3016	Authorized officer Wolff, G

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	BOYANOV B I ET AL: "Growth of epitaxial CoSi2 on SiGe(001)" JOURNAL OF APPLIED PHYSICS, AMERICAN INSTITUTE OF PHYSICS. NEW YORK, US, vol. 86, no. 3, 1 August 1999 (1999-08-01), pages 1355-1362, XP012048329 ISSN: 0021-8979 abstract -----	1-28
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Information on patent family members

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